Photocoupler

K4N32 • K4N32A

These Photocouplers cosist of a Gallium Arsenide Infrared Emitting Diode and a Silicon NPN Photo Darlington transistor in a 6-pin package.

FEATURES

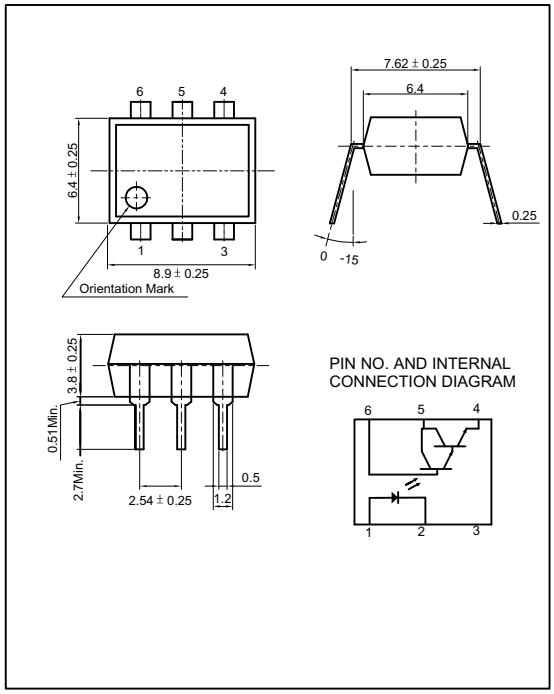
- Small Package Size
- Collector-Emitter Voltage : Min.30V
- Current Transfer Ratio : Type 1000% (at I_F=10mA, V_{CE}=10V)
- Electrical Isolation Voltage : AC2500V_{rms}
- UL Recognized File No. E107486

APPLICATIONS

- Interface between two circuits of different potential
- Telephone Line Receiver, CMOS Logic Interface
- Power Supply Regulators

DIMENSION

(Unit : mm)



MAXIMUM RATINGS

(Ta=25℃)

Parameter		Symbol	Rating	Unit
Input	Forward Current	I_F	80	mA
	Reverse Voltage	V_R	5	V
	Peak Forward Current *1	I_{FP}	3	A
	Power Dissipation	P_D	150	mW
Output	Collector-Emitter Breakdown Voltage	BV_{CEO}	30	V
	Emitter-Collector Breakdown Voltage	BV_{ECO}	5	V
	Collector-Base Breakdown Voltage	BV_{ECO}	30	V
	Collector Current	I_C	100	mA
	Collector Power Dissipation	P_C	150	mW
Input to Output Isolation Voltage *2		V_{iso}	AC2500	V_{rms}
Storage Temperature		T_{stg}	-55~+125	℃
Operating Temperature		T_{opr}	-30~+100	℃
Lead Soldering Temperature *3		T_{sol}	260	℃
Total Power Dissipation		P_{tot}	250	mW

*1. Input current with 300㎲ pulse width, 2% duty cycle

*2. Measured at RH=40~60% for 1min

*3. 1/16 inch form case for 10sec

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ELECTRO-OPTICAL CHARACTERISTICS

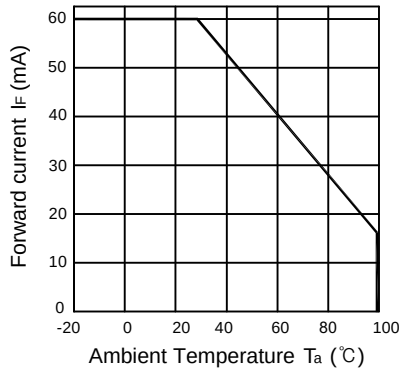
(Ta=25℃ , unless otherwise noted)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit.
Input	Forward Voltage	V_F	I_F=10mA	-	1.15	1.30	V
	Reverse Current	I_R	VR=5V	-	-	10	㎂
	Capacitance	C_T	V=0, f=1MHz	-	30	-	pF
Output	Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=1mA	35	-	-	V
	Emitter-Collector Breakdown Voltage	BV_{ECO}	I_E=0.1mA	5	-	-	V
	Collector-Base Breakdown Voltage	BV_{CBO}	I_C=0.1mA	30	-	-	V
	Collector Dark Current	I_{CEO}	I_F=0, V_{CE}=10V	-	-	100	nA
	Capacitance	C_{CE}	V_{CE}=0, f=1MHz	-	10	-	pF
Coupled	Current Transfer Ratio*4	CTR	I_F=10mA, V_{CE}=10V	500	-	-	%
	Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_F=50mA, I_C=2mA	-	-	1.0	V
	Input-Output Capacitance	C_{IO}	V=0, f=1MHz	-	1	-	pF
	Input-Output Isolation Resistance	R_{IO}	RH=40~60%, V=500V	-	10^{11}	-	Ω
	Turn-on Time	t_{on}	V_{CE}=10V, R_L=100Ω	-	-	5	㎲
	Turn-off Time	t_{off}	I_C=50mA, I_F=200mA	-	-	100	㎲

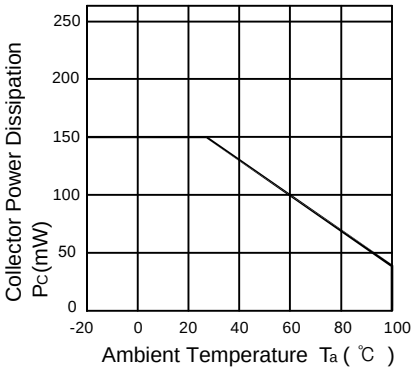
*4. CTR=(I_C/I_F) X 100 (%)

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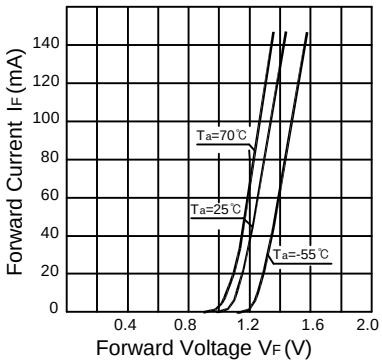
Forward Current vs. Ambient Temperature



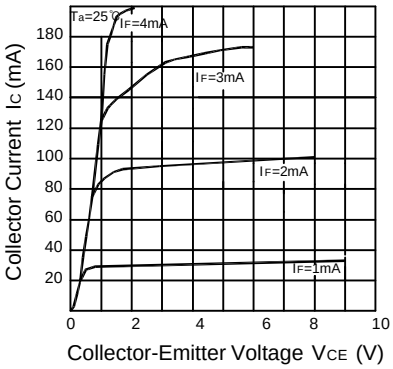
Collector Power Dissipation vs. Ambient Temperature



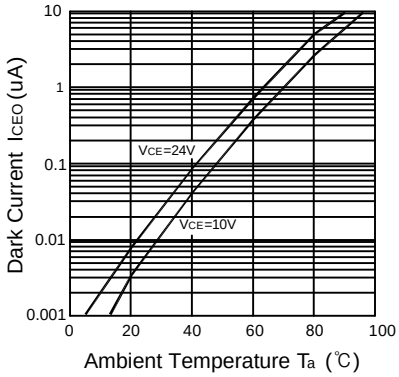
Forward Current vs. Forward Voltage



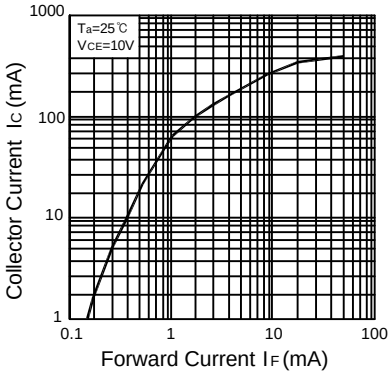
Collector Current vs. Collector-Emitter Voltage



Dark Current vs. Ambient Temperature



Collector Current vs. Forward Current



Switching Time Test Circuit

